

Amendment under article 34

1. (Amended) An impurity introducing method which comprising:
 - a step of introducing an impurity selected from a group consisting of B, As, P, Sb and In into a surface of a semiconductor substrate; and
 - a step of radiating inactive plasma to the surface of the semiconductor substrate after the impurity introducing step.
2. (Amended) The impurity introducing method according to claim 1, wherein the step of radiating the plasma includes a step of radiating plasma such that the impurity possesses a desired impurity profile in the semiconductor substrate.
3. (Amended) The impurity introducing method according to claim 1 or 2, wherein the step of radiating the plasma includes a step of radiating plasma which contains at least one kind of rare gas element.
4. (Amended) The impurity introducing method according to claim 3, wherein the step of radiating the plasma includes a step of radiating He plasma.
5. (Amended) The impurity introducing method according to claim 1 or 2, wherein the step of radiating the plasma includes a step of radiating plasma which contains hydrogen.
6. (Amended) The impurity introducing method according to any

one of claims 1 to 5, wherein the step of introducing the impurity includes a plasma doping step.

7. (Amended) The impurity introducing method according to any
5 one of claims 1 to 5, wherein the step of introducing the impurity includes an ion implanting step.

8. (Amended) The impurity introducing method according to any
one of claims 1 to 5, wherein the step of introducing the impurity
10 includes a gas doping step.

9. (Amended) The impurity introducing method according to any
one of claims 1 to 8, wherein the semiconductor device is formed
to have the impurity profile in which the impurity concentration
15 at a depth position of 4nm is set to 1/10 or more of the impurity
concentration on the surface of the semiconductor device.

10. (Amended) The semiconductor device according to claim 9,
wherein the semiconductor device is formed to have the impurity
20 profile in which the impurity concentration at a depth position
of 7nm is set to 1/100 or more of the impurity concentration
on the surface of the semiconductor device.

[11] (Deleted)

25 [12] (Deleted)

[13] (Deleted)